**Preferred Device** 

### **Triacs**

### **Silicon Bidirectional Thyristors**

Designed primarily for full-wave ac control applications such as lighting systems, heater controls, motor controls and power supplies.

- Blocking Voltage to 800 Volts
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Gate Triggering Guaranteed in Four Modes
- High Current and Surge Ratings
- Device Marking: Logo, Device Type, e.g., MAC224A4, Date Code

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to 125°C, Sine Wave 50 to 60 Hz, Gate Open)  MAC224A4 MAC224A6 MAC224A8 MAC224A10	V <sub>DRM</sub> , V <sub>RRM</sub>	200 400 600 800	Volts
On–State RMS Current (T <sub>C</sub> = 75°C) <sup>(2)</sup> (Full Cycle Sine Wave 50 to 60 Hz)	I <sub>T(RMS)</sub>	40	A
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, T <sub>J</sub> = 125°C)	I <sub>TSM</sub>	350	Α
Circuit Fusing Considerations (t = 8.3 ms)	l <sup>2</sup> t	500	A <sup>2</sup> s
Peak Gate Current (Pulse Width ≤ 2.0 μsec; T <sub>C</sub> = 75°C)	I <sub>GM</sub>	± 2.0	Α
Peak Gate Voltage (Pulse Width ≤ 2.0 μsec; T <sub>C</sub> = 75°C)	V <sub>GM</sub>	±10	Volts
Peak Gate Power (Pulse Width ≤ 2.0 μsec; T <sub>C</sub> = 75°C)	Рам	20	Watts
Average Gate Power (T <sub>C</sub> = 75°C, t = 8.3 ms)	P <sub>G(AV)</sub>	0.5	Watts
Operating Junction Temperature Range	TJ	-40 to 125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to 150	°C
Mounting Torque	_	8.0	in. lb.

- (1) V<sub>DRM</sub>, V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- (2) This device is rated for use in applications subject to high surge conditions. Care must be taken to insure proper heat sinking when the device is to be used at high sustained currents. (See Figure 1 for maximum case temperatures.)

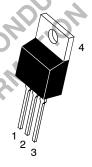


### **ON Semiconductor**

http://onsemi.com

# TRIACS 40 AMPERES RMS 200 thru 800 VOLTS





TO-220AB CASE 221A STYLE 4

PIN ASSIGNMENT		
1	Main Terminal 1	
2	Main Terminal 2	
3	Gate	
4	Main Terminal 2	

### **ORDERING INFORMATION**

Device	Package	Shipping
MAC224A4	TO220AB	500/Box
MAC224A6	TO220AB	500/Box
MAC224A8	TO220AB	500/Box
MAC224A10	TO220AB	500/Box

**Preferred** devices are recommended choices for future use and best overall value.

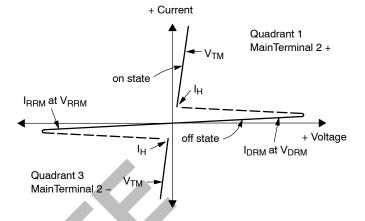
### THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance — Junction to Case — Junction to Ambient	R <sub>θJC</sub> R <sub>θJA</sub>	1.0 60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T <sub>L</sub>	260	°C

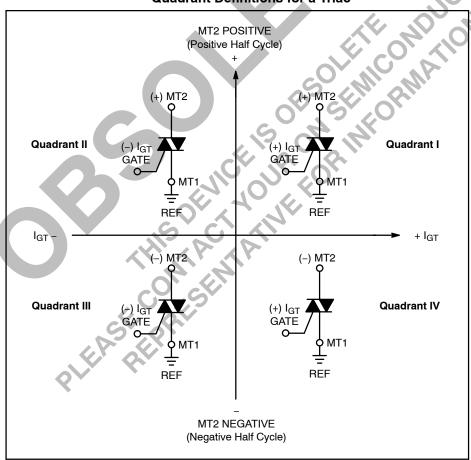
Characteristic	Symbol	Min	Тур	Max	Unit
FF CHARACTERISTICS		1		J	I
$\label{eq:peak_repetitive_Blocking_Current} \begin{array}{ll} \text{Peak Repetitive Blocking Current} \\ \text{(Rated V}_{DRM}, \text{V}_{RRM}; \text{Gate Open)} & \text{T}_{J} = 25^{\circ}\text{C} \\ \text{T}_{J} = 125^{\circ}\text{C} \end{array}$	I <sub>DRM,</sub> I <sub>RRM</sub>			10 2.0	μA mA
ON CHARACTERISTICS		<b>)</b>			
Peak On–State Voltage $(I_{TM}=\pm 56 \text{ A Peak, Pulse Width} \leqslant 2 \text{ ms, Duty Cycle} \leqslant 2\%)$	V <sub>TM</sub>		1.4	1.85	Volts
Gate Trigger Current (Continuous dc) $(V_D=12\ V,\ R_L=100\ \Omega) \\ MT2(+),\ G(+);\ MT2(+),\ G(-);\ MT2(+),\ G(-) \\ MT2(-),\ G(+)$	I <sub>GT</sub>	_	25 40	50 75	mA
Gate Trigger Voltage (Continuous dc) $ (V_D = 12 \ V, \ R_L = 100 \ \Omega) $ $ MT2(+), \ G(+); \ MT2(-), \ G(-); \ MT(+), \ G(-) $ $ MT2(-), \ G(+) $	V <sub>GT</sub>	CON	1.1 1.3	2.0 2.5	Volts
Gate Non-Trigger Voltage $(V_D = 12 \text{ V}, T_J = 125^{\circ}\text{C}, R_L = 100 \Omega)$ All Quadrants	V <sub>GD</sub>	0.2	_		Volts
Holding Current ( $V_D = 12 \text{ Vdc}$ , Gate Open, Initiating Current = $\pm 200 \text{ mA}$ )	ON II	_	30	75	mA
Gate Controlled Turn-On Time ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 56 A Peak, $I_G$ = 200 mA)	t <sub>gt</sub>	_	1.5	_	μs
YNAMIC CHARACTERISTICS	.(/,				
Critical Rate of Rise of Off-State Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform, T <sub>C</sub> = 125°C)	dv/dt	_	50	_	V/µs
Critical Rate of Rise of Commutation Voltage ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 56 A Peak, Commutating di/dt = 20.2 A/ms, Gate Unenergized, $T_C$ = 75°C)	dv/dt(c)	_	5.0		V/µs
di/dt = 20.2 A/ms, Gate Unenergized, T <sub>C</sub> = 75°C)					

## Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current



### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

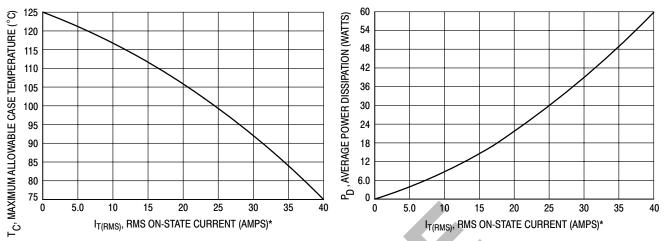


Figure 1. RMS Current Derating

Figure 2. On-State Power Dissipation

<sup>\*</sup>This device is rated for use in applications subject to high surge conditions. Care must be taken to insure proper heat sinking when the device is to be used at high sustained currents.

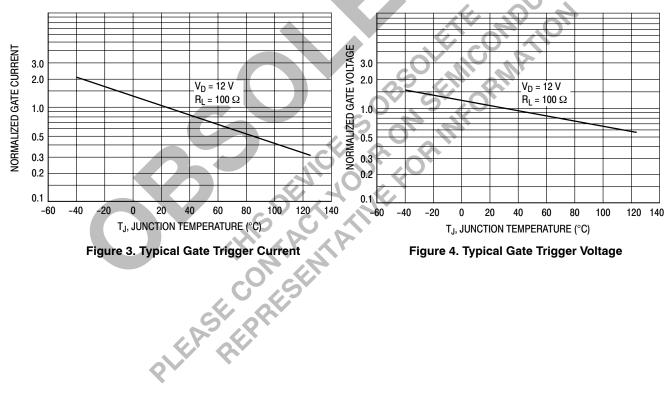
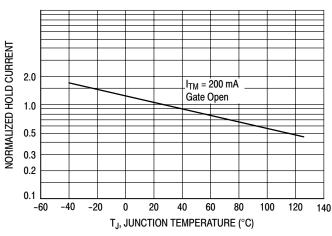


Figure 4. Typical Gate Trigger Voltage



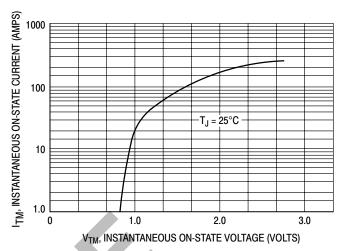
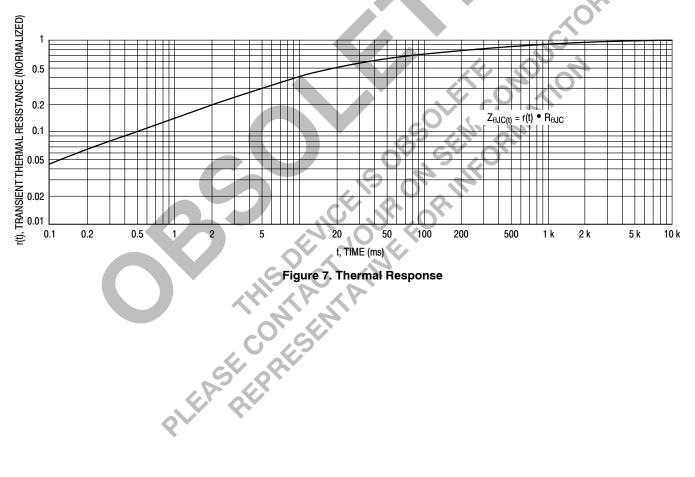


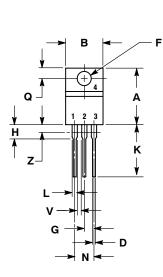
Figure 5. Typical Holding Current

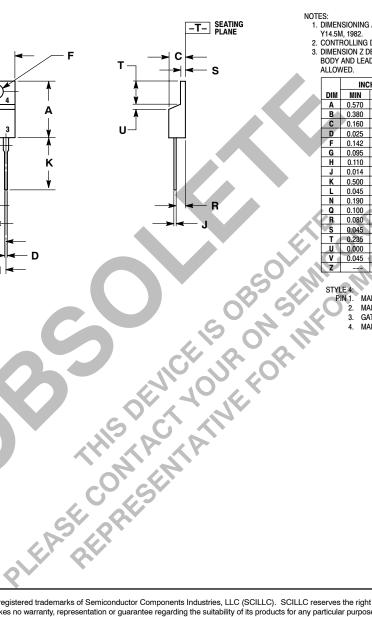
Figure 6. Typical On-State Characteristics



### PACKAGE DIMENSIONS

### **TO-220AB** CASE 221A-07 **ISSUE Z**





### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
   DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
٦	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
B	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T_	0.235	0.255	5.97	6.47
F	0.000	0.050	0.00	1.27
۸	0.045		1.15	
Z		0.080		2.04

MAIN TERMINAL 1

MAIN TERMINAL 2

GATE

MAIN TERMINAL 2

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